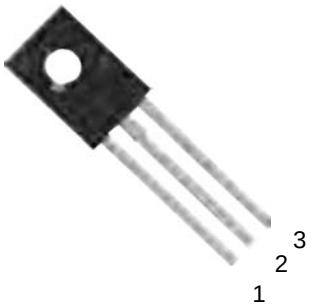
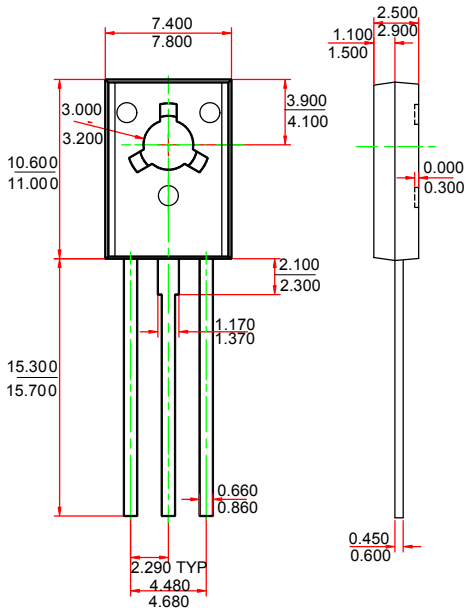
2SC1162(NPN)

TO-126 Transistor



1. EMITTER
2. COLLECOTR
3. BASE

TO-126



Dimensions in inches and (millimeters)

Features

✧ **Low frequency power amplifier**

MAXIMUM RATINGS (T_A=25℃ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Emitter Voltage	35	V
V_{CEO}	Collector-Emitter Voltage	35	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	2.5	A
Pc	Collector Power Dissipation	0.75	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55-150	℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C =1mA,I_E=0	35			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C =10mA,I_B=0	35			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=1mA ,I_C=0	5			V
Collector cut-off current	I_{CBO}	V_{CB}=35V,I_E=0			20	μA
Emitter cut-off current	I_{EBO}	V_{EB}=5V,I_C=0			20	μA
DC current gain	h_{FE1}	V_{CE}=2V,I_C=0.5A	60		320	
	h_{FE2}	V_{CE}=2V,I_C=1.5A *	20			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=2A,I_B=200mA			1	V
Base-collector voltage	V_{BE}	V_{CE}=2V,I_C=1.5A			1.5	V
Transition frequency	f_T	V_{CE}=2V,I_C=200mA		180		MHz

*pulse test

CLASSIFICATION OF h_{FE1}

Rank	B	C	D
Range	60-120	100-200	160-320

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Typical Characteristics